

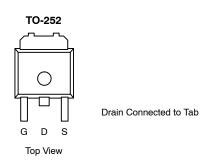
## H5N03LA-VB Datasheet

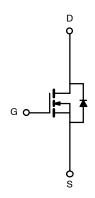
# N-Channel 20-V (D-S)175 $^{\circ}$ C MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$r_{DS(on)}\left(\Omega\right)$	I <sub>D</sub> (A) <sup>a</sup>			
20	0.0045 @ V <sub>GS</sub> = 4.5 V	100			
	0.006 @ V <sub>GS</sub> = 2.5 V	90			

#### **FEATURES**

- Trench Power MOSFET
- 175°C Maximum Junction Temperature
- 100% R<sub>g</sub> Tested





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (TA = 25°C UNLESS OTHERWISE NOTED)							
Parameter		Symbol	Limit	Unit			
Drain-Source Voltage		V <sub>DS</sub>	20				
Gate-Source Voltage		V <sub>GS</sub>	±15				
	T <sub>C</sub> = 25°C		100				
Continuous Drain Current <sup>a</sup>	T <sub>C</sub> = 100°C	I <sub>D</sub>	80				
Pulsed Drain Current		I <sub>DM</sub>	200	A			
Continuous Source Current (Diode Conduction) <sup>a</sup>		Is	65				
	T <sub>C</sub> = 25°C	_	71				
Maximum Power Dissipation	T <sub>A</sub> = 25°C	P <sub>D</sub>	8.3 <sup>b, c</sup>	W			
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 175	°C			

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Typical	Maximum	Unit			
	t ≤ 10 sec.		15	18	°C/W		
Maximum Junction-to-Ambient <sup>b</sup>	Steady State	R <sub>thJA</sub>	40	50			
Maximum Junction-to-Case	R <sub>thJC</sub>	1.75	2.1				

### Notes

- a. Package Limited
- b. Surface Mounted on 1" x 1" FR4 Board
- c.  $t \le 10 \text{ sec}$

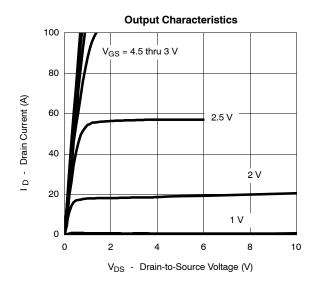


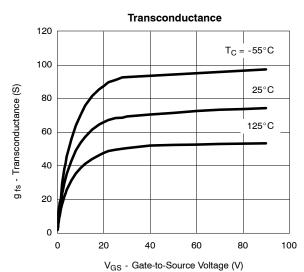
Parameter	Symbol	Test Condition	Min	Typ <sup>a</sup>	Max	Unit
Static	- <del>1</del>		<b>-</b>	•		
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS}$ = 0 V, $I_D$ = 250 $\mu A$	20			
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	0.5		1.5	٧
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			±100	nA
	_	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V			1	μΑ
Zero Gate Voltage Drain Current	DSS	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125°C			50	
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	100			Α
		$V_{GS} = 4.5 \text{ V}, I_D = 20 \text{ A}$		0.0045	ı	
Drain-Source On-State Resistance <sup>b</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 20 A, T <sub>J</sub> = 125°C		0.0055		Ω
	`	$V_{GS} = 2.5 \text{ V}, I_D = 20 \text{ A}$		0.006		1
Forward Transconductanceb	9 <sub>fs</sub>	$V_{DS} = 5 \text{ V}, I_D = 40 \text{ A}$	20			S
Dynamic <sup>a</sup>						•
Input Capacitance	C <sub>iss</sub>			3660		pF
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = 20 \text{ V}, f = 1 \text{ MHz}$		730		
Reverse Transfer Capacitance	C <sub>rss</sub>			375		
Total Gate Charge <sup>c</sup>	Qg			26	35	nC
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS}$ = 10 V, $V_{GS}$ = 4.5 V, $I_D$ = 40 A		5		
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			7		
Gate Resistance	R <sub>g</sub>		1		3.7	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			20	35	
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 10 \text{ V. R}_1 = 0.25 \Omega$		120	190	ns
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$\begin{aligned} V_{DD} &= 10 \text{ V, } R_L = 0.25 \ \Omega \\ I_D &\cong 40 \text{ A, } V_{GEN} = 4.5 \text{ V, } R_G = 2.5 \ \Omega \end{aligned}$		45	70	
Fall Time <sup>c</sup>	t <sub>f</sub>			20	35	
Source-Drain Diode Ratings an	d Characteristi	c (T <sub>C</sub> = 25°C)		•		•
Pulsed Current	I <sub>SM</sub>				100	А
Diode Forward Voltage <sup>b</sup>	V <sub>SD</sub>	$I_F = 100 \text{ A}, V_{GS} = 0 \text{ V}$		1.2	1.5	V
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 40 A, di/dt = 100 A/μs		35	70	ns

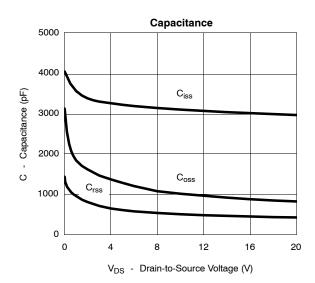
- Notes a. Guaranteed by design, not subject to production testing. b. Pulse test; pulse width  $\leq 300~\mu s$ , duty cycle  $\leq 2\%$ . c. Independent of operating temperature.

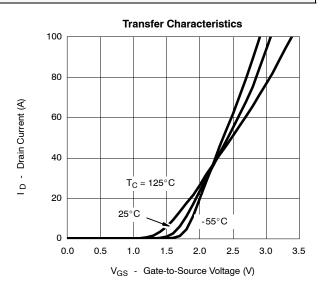


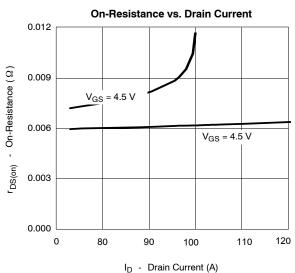
### TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

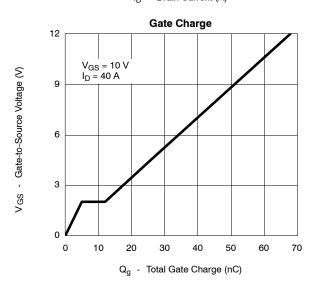






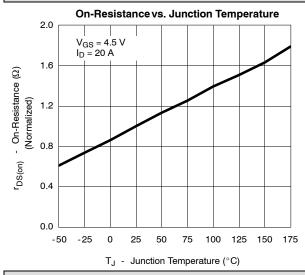


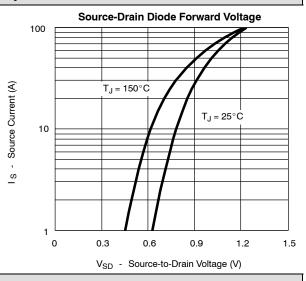




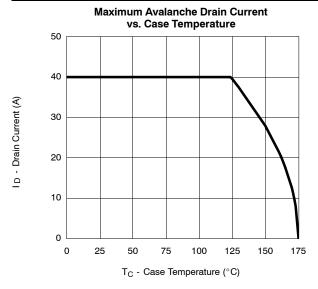


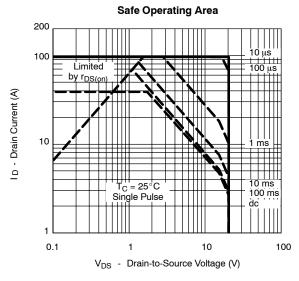
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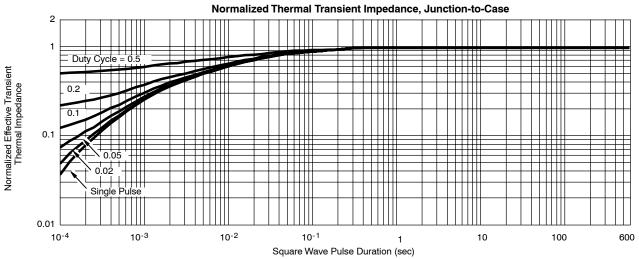




#### **THERMAL RATINGS**

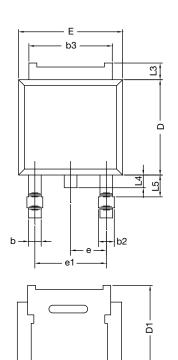


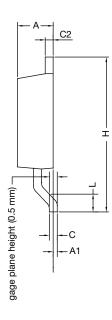






# **TO-252AA CASE OUTLINE**





	MILLIMETERS		INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.18	2.38	0.086	0.094	
A1	ı	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	5.21	-	0.205	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	1	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC 0.090 BSC		BSC	
e1	4.56	BSC	0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	=	1.02	-	0.040	
L5	1.14	1.52	0.045	0.060	
ECN: X12-0247-Rev. M, 24-Dec-12 DWG: 5347					

### Note

• Dimension L3 is for reference only.

服务热线:400-655-8788

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